

12/18/02  
ar**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Sang Ick LEE et al. ]

Group Art Unit: 2823

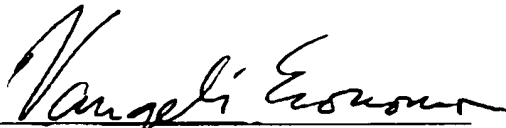
Serial No.: 09/994,284 ]

Examiner: Pham, Thanh V. ]

Filed: 26 November 2001 ]

**AMENDMENT AFTER FINAL** ]For: METHOD OF FORMING METAL ]  
GATE IN SEMICONDUCTOR ]  
DEVICE ]**EXPEDITED PROCEDURE****Certification under 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence, and all documents referred to herein as being attached, are being transmitted by facsimile to the United States Patent and Trademark Office at the following facsimile number: (703) 308-7382, to the attention of Examiner Pham, and addressed to the Commissioner for Patents, Washington, D.C. 20231 on December 13, 2002.

  
Vangelis Economou, Reg. No. 32,341

Commissioner for Patents  
Washington, D.C. 20231

**RESPONSE UNDER 37 C.F.R. §1.116**

In response to the Office Action dated October 15, 2002, please consider the following:

**REMARKS**

Reconsideration is respectfully requested.

**FAX RECEIVED**

DEC 13 2002

TECHNOLOGY CENTER 2800